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MM74HC86 Quad 2-Input Exclusive OR Gate

General Description

The MM74HC86 EXCLUSIVE OR gate utilizes advanced silicon-gate CMOS technology to achieve operating speeds similar to equivalent LS-TTL gates while maintaining the low power consumption and high noise immunity characteristic of standard CMOS integrated circuits. These gates are fully buffered and have a fanout of 10 LS-TTL loads. The 74HC logic family is functionally as well as pin out compatible with the standard 74LS logic family. All

September 1983

Revised February 1999

inputs are protected from damage due to static discharge by internal diode clamps to $V_{\mbox{CC}}$ and ground.

Features

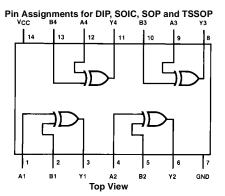
- Typical propagation delay: 9 ns
- Wide operating voltage range: 2–6V
- Low input current: 1 µA maximum
- Low quiescent current: 20 µA maximum (74 Series)
- Output drive capability: 10 LS-TTL loads

Ordering Code:

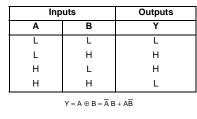
| Order Number | Package Number | Package Description |
|--------------|----------------|--|
| MM74HC86M | M14A | 14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-120, 0.150" Narrow |
| MM74HC86SJ | M14D | 14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide |
| MM74HC86MTC | MTC14 | 14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide |
| MM74HC86N | N14A | 14-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide |

Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.

Connection Diagram



Truth Table



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Absolute Maximum Ratings(Note 1) (Note 2)

| () | |
|--|-----------------------------------|
| Supply Voltage (V _{CC}) | -0.5 to +7.0V |
| DC Input Voltage (V _{IN}) | –1.5 to V _{CC} +1.5V |
| DC Output Voltage (V _{OUT}) | –0.5 to V _{CC} +0.5V |
| Clamp Diode Current (I _{IK} , I _{OK}) | ±20 mA |
| DC Output Current, per pin (I _{OUT}) | ±25 mA |
| DC V_{CC} or GND Current, per pin (I _{CC}) | ±50 mA |
| Storage Temperature Range (T _{STG}) | $-65^{\circ}C$ to $+150^{\circ}C$ |
| Power Dissipation (P _D) | |
| (Note 3) | 600 mW |
| S.O. Package only | 500 mW |
| Lead Temperature (TL) | |
| (Soldering 10 seconds) | 260°C |
| | |

Recommended Operating Conditions

| | Min | Max | Units |
|---|----------|----------|----------|
| Supply Voltage (V _{CC}) | 2 | 6 | V |
| DC Input or Output Voltage | 0 | V_{CC} | V |
| (V _{IN} , V _{OUT}) | | | |
| Operating Temperature Range (T _A) | -40 | +85 | °C |
| Input Rise or Fall Times | | | |
| $(t_r, t_f) V_{CC} = 2.0V$ | | 1000 | ns |
| $V_{CC} = 4.5V$ | | 500 | ns |
| $V_{CC} = 6.0V$ | | 400 | ns |
| Note 1: Absolute Maximum Ratings are those va | alues be | yond wh | ich dam- |

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground. Note 3: Power Dissipation temperature derating — plastic "N" package: – 12 mW/°C from 65°C to 85°C.

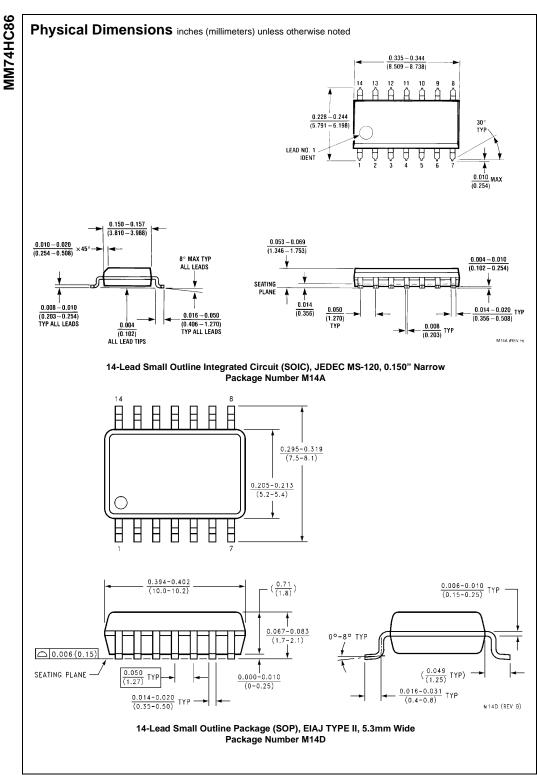
DC Electrical Characteristics (Note 4)

| Symbol | Parameter | Conditions | v _{cc} | T _A = | 25°C | $T_A=-40$ to $85^\circ C$ | $T_A = -55 \ to \ 125^\circ C$ | Units |
|-----------------|--------------------|--------------------------------------|-----------------|------------------|------|---------------------------|--------------------------------|-------|
| Symbol | Falameter | Conditions | •00 | Тур | | Guaranteed L | imits | Units |
| VIH | Minimum HIGH Level | | 2.0V | | 1.5 | 1.5 | 1.5 | V |
| | Input Voltage | | 4.5V | | 3.15 | 3.15 | 3.15 | V |
| | | | 6.0V | | 4.2 | 4.2 | 4.2 | V |
| VIL | Maximum LOW Level | | 2.0V | | 0.5 | 0.5 | 0.5 | V |
| | Input Voltage | | 4.5V | | 1.35 | 1.35 | 1.35 | V |
| | | | 6.0V | | 1.8 | 1.8 | 1.8 | V |
| V _{OH} | Minimum HIGH Level | $V_{IN} = V_{IH} \text{ or } V_{IL}$ | | | | | | |
| | Output Voltage | $ I_{OUT} \le 20 \ \mu A$ | 2.0V | 2.0 | 1.9 | 1.9 | 1.9 | V |
| | | | 4.5V | 4.5 | 4.4 | 4.4 | 4.4 | V |
| | | | 6.0V | 6.0 | 5.9 | 5.9 | 5.9 | V |
| | | $V_{IN} = V_{IH} \text{ or } V_{IL}$ | | | | | | |
| | | I _{OUT} ≤ 4.0 mA | 4.5V | 4.2 | 3.98 | 3.84 | 3.7 | V |
| | | I _{OUT} ≤ 5.2 mA | 6.0V | 5.7 | 5.48 | 5.34 | 5.2 | V |
| V _{OL} | Maximum LOW Level | $V_{IN} = V_{IH} \text{ or } V_{IL}$ | | | | | | |
| | Output Voltage | $ I_{OUT} \le 20 \ \mu A$ | 2.0V | 0 | 0.1 | 0.1 | 0.1 | V |
| | | | 4.5V | 0 | 0.1 | 0.1 | 0.1 | V |
| | | | 6.0V | 0 | 0.1 | 0.1 | 0.1 | V |
| | | $V_{IN} = V_{IH} \text{ or } V_{IL}$ | | | | | | |
| | | $ I_{OUT} \le 4.0 \text{ mA}$ | 4.5V | 0.2 | 0.26 | 0.33 | 0.4 | V |
| | | I _{OUT} ≤5.2 mA | 6.0V | 0.2 | 0.26 | 0.33 | 0.4 | V |
| I _{IN} | Maximum Input | $V_{IN} = V_{CC}$ or GND | 6.0V | | ±0.1 | ±1.0 | ±1.0 | μA |
| | Current | | | | | | | |
| I _{CC} | Maximum Quiescent | $V_{IN} = V_{CC}$ or GND | 6.0V | | 2.0 | 20 | 40 | μA |
| | Supply Current | $I_{OUT} = 0 \ \mu A$ | | | | | | |

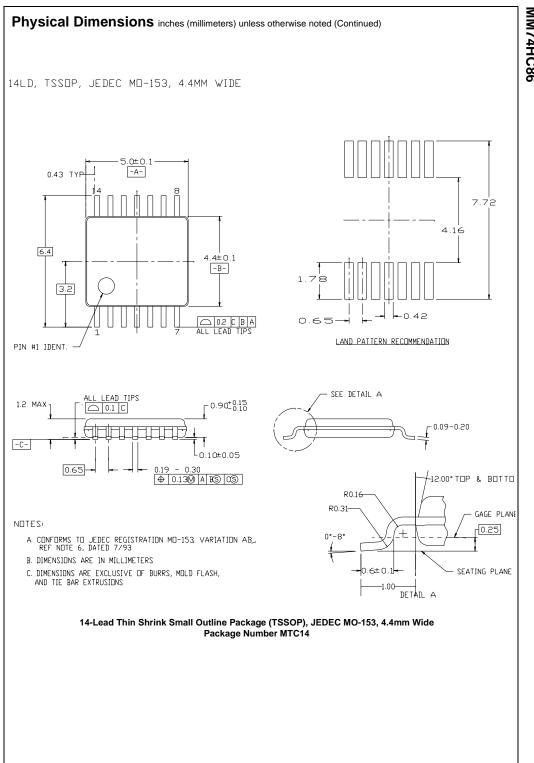
Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OL}) and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{H} and V_{L} occur at $V_{CC} = 5.5V$ and 4.5V respectively. (The V_{H} value at 5.5V is 3.85V.) The worst case leakage current (I_{N} , I_{CC} , and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

| DelayAC Electrical Characteristics $V_{CC} = 2.0V$ to 6.0V, $C_L = 50$ pF, $t_r = t_f = 6$ ns (unless otherwise specified)T _A = 25°CT _A = -40 to 85°CT _A = -55 to 125°CUnitsSymbolParameterConditions V_{CC} $T_A = 25°C$ $T_A = -40$ to 85°C $T_A = -55$ to 125°CUnitsHL, t_{PLH} Maximum Propagation2.0V60120151179nsDelay4.5V12243036nsLH, t_{HL} Maximum Output Rise2.0V307595110nsand Fall Time4.5V8151922nsPDPower Dissipation(per gate)25000INMaximum Input5101010pFCapacitance(Note 5)5101010pF | Delay AC Electrical Characteristics V _{CC} = 2.0V to 6.0V, C _L = 50 pF, t _r = t _f = 6 ns (unless otherwise specified) T _A = 25°C T _A = -40 to 85°C T _A = -55 to 125°C Unit Symbol Parameter Conditions V _{CC} T _A = 25°C T _A = -40 to 85°C T _A = -55 to 125°C Unit tpHL, tpLH Maximum Propagation 2.0V 60 120 151 179 ns ttLH, tpLH Maximum Output Rise 2.0V 6.0V 10 20 26 30 ns tTLH, tTHL Maximum Output Rise 2.0V 30 75 95 110 ns CPD Power Dissipation (and Fall Time (per gate) 25 10 10 pF Clapacitance (Note 5) (per gate) 5 10 10 pF | Symbo | $T_{A} = 25^{\circ}C, C_{L} = 15 \text{ pF}, t_{r} = t_{f} = 0$ | | c | Conditions | i | Тур | Guaranteed Limit | Units |
|--|---|-------------------------------------|---|------------------------|-----------------------|------------------|------|------------------------------|-------------------------------|-------|
| $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | $ \begin{array}{c c c c c c c c c c c c c c c c c c c $ | t _{PHL} , t _{PLH} | | 1 | | | | 12 | 20 | ns |
| SymbolParameterConditions V_{CC} $\overline{T_A = -55 \text{ co} 25^{\circ}\text{C}}$ $\overline{T_A = -40 \text{ to} 85^{\circ}\text{C}}$ $\overline{T_A = -55 \text{ to} 125^{\circ}\text{C}}$ $\overline{V_{IT} = -40 \text{ to} 85^{\circ}\text{C}}$ $\overline{T_A = -55 \text{ to} 125^{\circ}\text{C}}$ $\overline{V_{IT} = -40 \text{ to} 85^{\circ}\text{C}}$ $\overline{T_A = -55 \text{ to} 125^{\circ}\text{C}}$ $\overline{V_{IT} = -40 \text{ to} 85^{\circ}\text{C}}$ $\overline{T_A = -55 \text{ to} 125^{\circ}\text{C}}$ $\overline{V_{IT} = -40 \text{ to} 85^{\circ}\text{C}}$ $\overline{T_A = -55 \text{ to} 125^{\circ}\text{C}}$ $\overline{V_{IT} = -55 \text{ to} 125^{\circ}\text{C}}$ V_{I | SymbolParameterConditions V_{CC} $T_A = -40 \text{ to } 85^\circ C$ $T_A = -55 \text{ to } 125^\circ C$ $T_A = -55 to $ | | | | apposition) | | | | | |
| Typ Guaranteed Limits HL. t_{PLH} Maximum Propagation 2.0V 60 120 151 179 ns Delay 4.5V 12 24 30 36 ns LH. t_{THL} Maximum Output Rise 2.0V 30 75 95 110 ns and Fall Time 4.5V 8 15 19 22 ns PD Power Dissipation (per gate) 25 10 10 10 pF IN Maximum Input Capacitance 5 10 10 10 pF | Tube Type Guaranteed Limits PHL: t_{PLH} Maximum Propagation 2.0V 60 120 151 179 ns Delay 4.5V 12 24 30 36 ns TLH: t_{THL} Maximum Output Rise 2.0V 30 75 95 110 ns and Fall Time 4.5V 8 15 19 22 ns 6.0V 7 13 16 19 ns CPD Power Dissipation (per gate) 25 - - - - - CIN Maximum Input 5 10 10 10 pF Note 5: CPD determines the no load dynamic power consumption, PD = CPD VCC ² f + I _{CC} V _{CC} , and the no load dynamic current consumption, - - - - - | | | | | T _A = | 25°C | $T_A = -40$ to $85^{\circ}C$ | $T_A = -55$ to $125^{\circ}C$ | Unite |
| $ \begin{array}{ c c c c c c c c } \hline \begin{tabular}{ c c c c c c c } \hline \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$ | $\begin{array}{ c c c c c c c } \hline \mbox{Delay} & \mbox{$4.5V$} & \mbox{12} & \mbox{24} & \mbox{30} & \mbox{36} & \mbox{ns} \\ \hline \mbox{TLH, t_{THL}} & \mbox{Maximum Output Rise} & \mbox{$2.0V$} & \mbox{30} & \mbox{75} & \mbox{95} & \mbox{110} & \mbox{ns} \\ \hline \mbox{$and Fall Time$} & \mbox{$4.5V$} & \mbox{8} & \mbox{15} & \mbox{19} & \mbox{22} & \mbox{ns} \\ \hline \mbox{$and Fall Time$} & \mbox{$4.5V$} & \mbox{8} & \mbox{15} & \mbox{19} & \mbox{22} & \mbox{ns} \\ \hline \mbox{$and Fall Time$} & \mbox{$4.5V$} & \mbox{8} & \mbox{15} & \mbox{19} & \mbox{22} & \mbox{ns} \\ \hline \mbox{$chov$} & \mbox{$chov$} & \mbox{10} & \mbox{10} & \mbox{10} & \mbox{19} & \mbox{ns} \\ \hline \mbox{$chov$} & \mbox{$chov$} & \mbox{10} & \mbox{10} & \mbox{10} & \mbox{19} & \mbox{ns} \\ \hline \mbox{$chov$} & \mbox{$chov$} & \mbox{ns} & \mbox{10} & \mbox{10} & \mbox{ns} & \mbox{ns} \\ \hline \mbox{$chov$} & \mbox{ns} & $ | Cymber | i urumeter | Conditions | | Тур | | Guaranteed L | imits | 01110 |
| $ \begin{array}{ c c c c c c c } \hline \begin{tabular}{ c c c c c c c } \hline & & & & & & & & & & & & & & & & & & $ | $ \begin{array}{ c c c c c c c c } \hline \begin{tabular}{ c c c c c c c c c c } \hline \begin{tabular}{ c c c c c c c c c c c c c c c c c c c$ | _{PHL} , t _{PLH} | Maximum Propagation | | 2.0V | 60 | 120 | 151 | 179 | ns |
| LH, t THLMaximum Output Rise and Fall Time2.0V307595110nsPD PD Capacitance (Note 5)Per gate)25151922nsIN CapacitanceMaximum Input Capacitance5101010pFNote 5: CPD determines the no load dynamic power consumption, PD DCPD CPDCC2^2 f + ICC V_{CC}. and the no load dynamic current consumption, | LH- t THLMaximum Output Rise and Fall Time2.0V307595110ns $_{12H}$ t rmand Fall Time $\frac{2.0V}{4.5V}$ 8151922ns $_{PD}$ Power Dissipation Capacitance (Note 5)(per gate)2525pF $_{1N}$ Maximum Input Capacitance5101010pFNote 5: C PD determines the no load dynamic power consumption, PD = C PD VCc2 f + ICC VCc, and the no load dynamic current consumption,5101010 | | Delay | | 4.5V | 12 | 24 | 30 | 36 | ns |
| and Fall Time $4.5V$ 8151922nsPDPower Dissipation Capacitance (Note 5)(per gate)251619nsINMaximum Input Capacitance5101010pFNote 5: C _{PD} determines the no load dynamic power consumption, P _D = C _{PD} V _{CC} ² f + I _{CC} V _{CC} , and the no load dynamic current consumption, | and Fall Time $4.5V$ 8151922ns P_D Power Dissipation Capacitance (Note 5)(per gate)251619ns N_N Maximum Input Capacitance5101010pFNote 5: C _{PD} determines the no load dynamic power consumption, P _D = C _{PD} V _{CC} ² f + I _{CC} V _{CC} , and the no load dynamic current consumption, | | | | | | | | | ns |
| POPower Dissipation Capacitance (Note 5)(per gate) 25 1619nsINMaximum Input Capacitance5101010pFNote 5: C _{PD} determines the no load dynamic power consumption, P _D = C _{PD} V _{CC} ² f + I _{CC} V _{Cc} , and the no load dynamic current consumption,F | Power Dissipation Capacitance (Note 5)(per gate) $6.0V$ 7131619nsNMaximum Input Capacitance(per gate)2525Power DissipationpFNMaximum Input Capacitance5101010pFNote 5: C _{PD} determines the no load dynamic power consumption, P _D = C _{PD} V _{CC} ² f + I _{CC} V _{CC} , and the no load dynamic current consumption,5 | LH, t _{THL} | | | | | | 95 | | ns |
| PD Power Dissipation (per gate) 25 pF Capacitance (Note 5) Maximum Input Capacitance 5 10 10 pF Note 5: C _{PD} determines the no load dynamic power consumption, P _D = C _{PD} V _{CC} ² f + I _{CC} V _{CC} , and the no load dynamic current consumption, PF | PD Power Dissipation (per gate) 25 pF Capacitance (Note 5) (per gate) 25 10 10 pF IN Maximum Input Capacitance 5 10 10 10 pF Note 5: C _{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, F | | and Fall Time | | | | | | | ns |
| Capacitance (Note 5) 5 10 10 pF IN Maximum Input Capacitance 5 10 10 10 pF Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, | Capacitance (Note 5) Solution IN Maximum Input Capacitance 5 10 10 pF Note 5: C _{PD} determines the no load dynamic power consumption, P _D = C _{PD} V _{CC} ² f + I _{CC} V _{CC} , and the no load dynamic current consumption, 5 10 10 pF | | | | 6.0V | | 13 | 16 | 19 | |
| IN Maximum Input Capacitance 5 10 10 pF Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, | IN Maximum Input Capacitance 5 10 10 pF Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, P | PD | | (per gate) | | 25 | | | | pF |
| Capacitance Capacitance Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, | Capacitance Capacitance Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, | | Capacitance (Note 5) | | | | | | | |
| Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, | Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, | | | | | | | | | |
| | | Note 5: C _{PI} | Capacitance determines the no load dynami | c power consumption, P | $D = C_{PD} V_{CC}^2$ | | | | | p⊢ |

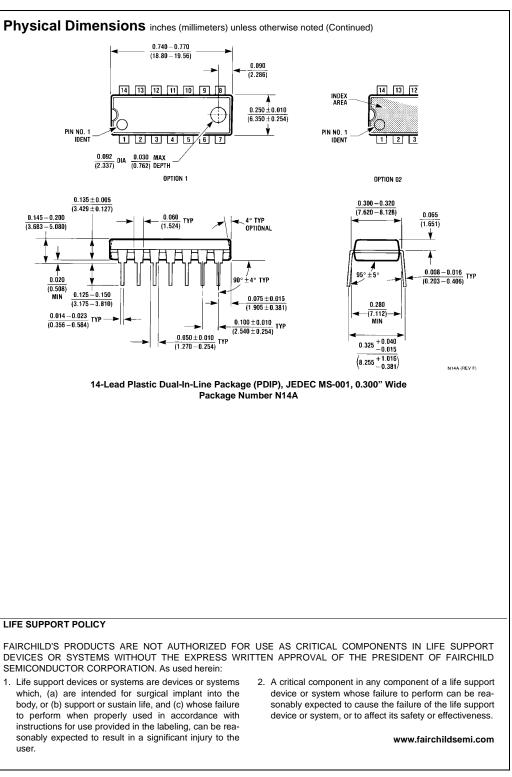
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